Advance Program Part II

LATE NEWS PAPERS

Tuesday, September 16

Oral Session

Room E

18:00 E-2-7L Optical Approach for Spin Detection in Quantum Nanostructures
B. Kaestner and J. Wunderlich, *Hitachi Cambridge Lab and Cabendish Lab, UK*

Wednesday, September 17

Room A

12:00 A-4-5L High Performance of 1.54 μm InGaAsP High-Power Tapered Laser Using High p-Doped Separate Confinement Layer and Strain Compensated Multiple Quantum Wells
D.C. Heo[1], I.K. Han[1], J.I. Lee[1] and J.C. Jeong[2], *[1]Korea Inst. of Science and Technology and [2]Korea Univ., Korea*

Room B

16:30 B-5-6L Organic Thin-Film Transistors with Alignment-Free Printable Electrodes
M. Ando[1,2], H. Sasaki[2], M. Kawasaki[1,2], S. Imazeki[1,2] and T. Kamata[3], *[1]OITDA, [2]Hitachi, Ltd. and [3]AIST, Japan*

17:40 B-6-3L Vt drift of Cycled Two-Bit microFLASH® Cells
P. Zisman, Y. Roizin and M. Gutman, *Tower Semiconductor Ltd., Israel*

17:55 B-6-4L On the Read Stability of SSI Flash
C.-M. Liu, J. Dirga, B.G. Lee and P.V. Voorde, *Winbond Electronics Corp. of America, USA*

Room E

10:15 E-3-6L Electron Spin Relaxation during Transport in GaAs
Y. Sato[1], Y. Takahashi[2], Y. Kawamura[1,3] and H. Kawaguchi[1,2], *[1]CREST-JST, [2]Yamagata Univ. and [3]Osaka Prefecture Univ., Japan*

Room F

10:15 F-3-4L Uniformity Studies of MOCVD Grown AlGaN/GaN HEMTs on 100-mm Diameter Sapphire
S. Arulkumaran[1], M. Miyoshi[1,2], T. Egawa[1], H. Ishikawa[1] and T. Jimbo[1], *[1]Nagoya Inst. of Technology and [2]NGK Insulatros Ltd., Japan*

Room G

11:45 G-4-4L Fabrication of High-Density Wiring Interposer for 10 GHz 3D Packaging Using a Photosensitive Multiblock Copolymerized Polyimide
K. Kikuchi[1], S. Segawa[2], E.-S. Jung[1], Y. Nemoto[3], H. Nakagawa[1], K. Tokoro[1] and M. Aoyagi[1], *[1]AIST, [2]PI Research and Development Co., Ltd. and [3]ASET, Japan*

Poster Session (13:00-15:00)

OHGI

P2: Advanced Silicon Devices and Physics

P2-18L Monolithic Transformer Modeling Based on the 4-port Characterization Technique
S.-C. Wang, G.-W. Huang, S.-D. Wu, A.-S. Peng and M.-H. Cho, *National Nano Device Labs, Taiwan*

P2-19L Improved Modeling Technique for On-Chip Silicon Spiral Inductors
M.-H. Cho, G.-W. Huang, K.-M. Chen, S.-Y. Wen and S.-C. Wang, *National Nano Device Labs, Taiwan*

P3: Silicon Process / Materials Technologies

P3-20L A Novel Process for Oxynitride by Post-Oxidation of NH_3 Plasma Nitridation
C.S. Lai and K.M. Fan, *Chang Gung Univ., Taiwan*

P3-21L Origin of Interfacial Reaction Constant for Si Thermal Oxidation
T. Akiyama[1,2] and H. Kageshima[1], *[1]NTT Corp. and [2]Mie Univ., Japan*

P4: New Materials and Characterization

P4-19L Near-Field Raman Microscopy of Si and Si-Based Structures Using AFM-Tip-Induced Breaking of Selection Rules
V. Poborchii, T. Tada and T. Kanayama, *MIRAI-ASRC, AIST, Japan*

P8: Quantum Nanostructure Devices and Physics

P8-11L Demonstration of Enhanced Tunneling Magneto Resistance Ratio for a Magnetic Tunnel Junction Connected in Parallel with a Tunnel Diode
T. Uemura, S. Honma, T. Marukame and M. Yamamoto, *Hokkaido Univ., Japan*

P9: Silicon-on-Insulator Technologies

P9-9L Patterned SIMOX SOI Materials with High Degree of Surface Planarity and Low Defect Density
Y. Dong[1], X. Wang[1,2], M. Chen[1,2], J. Chen[1], X. Wang[1,3], W. Yi[1,3], B. Jin[1] and E. Zhang[1], *[1]SIMIT, Chinese Academy of Sciences, [2]Shanghai Simgui Technology Co., Ltd. and [3]Grate Semiconductor Manufacturing Corp., China*

P9-10L A Surface-Potential-Based Cylindrical Surrounding-Gate MOSFET Model
S. Amakawa[1], K. Nakazato[2] and H. Mizuta[2], *[1]Univ. of Cambridge and [2]Hitachi Cambridge Lab, UK*

P11: SiGe/III-V/III-N Devices and Circuits for Wireless and Optical Communications

P11-5L Dynamic Thermal Characterization and Modeling of Silicon Bipolar Junction Transistors using Pulsed RF Measurement System
G.-W. Huang, A.-S. Peng, K.-M. Chen and L.-H. Chang, *National Nano Device Labs, Taiwan*

P13: Organic Semiconductor Devices and Materials

P13-7L Passivation of Organic Light Emitting Diodes with Plasma Polymerized p-Xylene Thin Films Deposited by PECVD
S. Sohn, S. Kho, D. Cho, J. Kim and D. Jung, *Sungkyunkwan Univ., Korea*

P13-8L Field Effect Transistors Formed with Thin Films of Alkyl Substituted Hexabenzocoronene
T. Minakata[1,2], [1]OITDA and [2]Asahi Kasei Corp., Japan

P13-9L Bottom Contact Organic Thin-Film Transistors with Reduced Contact Resistance
M. Kawasaki[1,2], S. Imazeki[1,2], T. Kamata[3] and M. Ando[1,2], *[1]OITDA, [2]Hitachi, Ltd. and [3]AIST, Japan*

Thursday, September 18

Oral Session

Room B

16:30 B-10-5L High Performance 45nm CMOS Technology with 20nm Multi-Gate Devices
Z. Krivokapic, C. Tabery, W. Maszara, Q. Xiang and M.-R. *Lin, AMD, USA*

16:45 B-10-6L Double Gate MOSFET by ESS (Empty Space in Silicon) Architecture
T. Sato, H. Nii, M. Hatano, Y. Kato, K. Ishigo, K. Takenaka, H. Hayashi, T. Hirano, K. Ida, T. Watanabe, N. Aoki, K. Ino, S. Kawanaka, I. Mizushima and Y. Tsunashima,
Toshiba Corp., Japan

Room D

9:05 D-7-0L Simultaneous Formation of Multi-Wall Carbon Nanotubes and their Low-Resistance Ohmic Contacts for Future ULSI via Interconnects
M. Nihei, A. Kawabata, M. Horibe and Y. Awano, *Fujitsu Ltd., Japan*

11:25 D-8-3L Characterization of Hafnium Diffusion into Thermally-Grown SiO_2 on Si(100)
M. Yamaoka , A. Ohta and S. Miyazaki,
Hiroshima Univ., Japan

11:40 D-8-4L Nanoscale Profiling of Surface Potential Across Silicon p-n Junctions by Scanning Resonance Tunneling Spectroscopy
L. Bolotov, T. Okui, H. Itoh and T. Kanayama,
MIRAI AIST, Japan

11:55 D-8-5L Advanced SiGe-Free Strained Si on Insulator Substrates: Thermal Stability and Carrier Mobility Enhancement
T.A. Langdo, M. Erdtmann, C.W. Leitz, M.T. Currie, A. Lochtefeld, Z. Cheng, J.A. Carlin, V.K. Yang, C.J. Vineis, C. Major, G. Braithwaite, H. Badawi and M.T. Bulsara,
AmberWave Systems Corp., USA

Room E

14:30 E-9-5L Improved Electron Emission Properties of Screen-Printed Carbon Nanotube Film by Hydrogen Plasma Surface Treatment
T. Feng[1], J. Zhang[1], X. Wang[1], X. Liu[1], S. Zou[1], Q. Li[2] and J.Xu[2], *[1]Shanghai Inst. of Mircosystem and Information Technology and [2]East China Normal Univ., China*

Room G

14:00 G-9-2L Non-Recessed-Gate Enhancement-Mode AlGaN/GaN HEMTs with High RF Performance
A. Endoh[1], Y. Yamashita[1], K. Ikeda[1], M. Higashiwaki[2], K. Hikosaka[1], T. Matsui[2], S. Hiyamizu[3] and T. Mimura[1], *[1]Fujitsu Labs Ltd., [2]Communications Research Lab and [3]Osaka Univ., Japan*

Withdrawn

Thursday, September 18

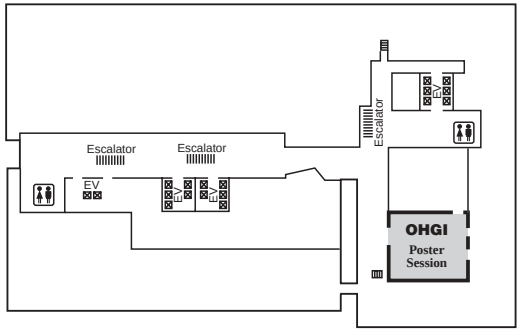
Room G

14:00 G-9-2 Gate Direction of AlGaN/GaN MODFET's with Low Temperature Coefficient of Threshold Voltage
H. Ishida, T. Murata, T. Matsuno, Y. Ikeda, Y. Hirose, Y. Uemoto and T. Tanaka,
Matsushita Electric Industrial Co., Ltd., Japan

Floor Map

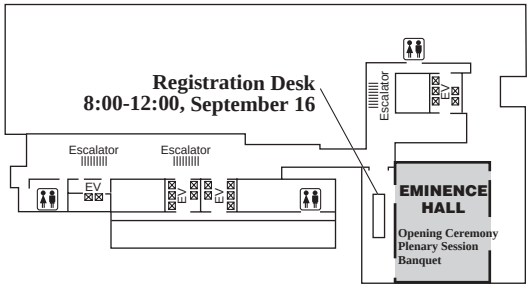
Poster Room

4F



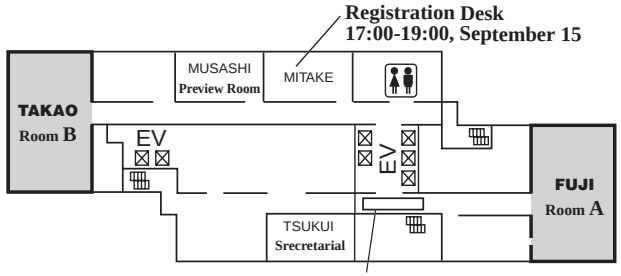
Eminence Hall

5F Opening Ceremony, Plenary Session and Banquet



Conference Room A, B

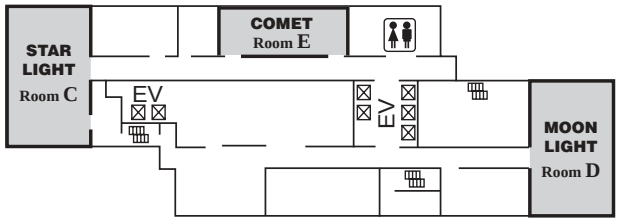
42F



Registration Desk
13:00-17:00, September 16
8:00-15:30, September 17, 18
8:00-13:30, September 19

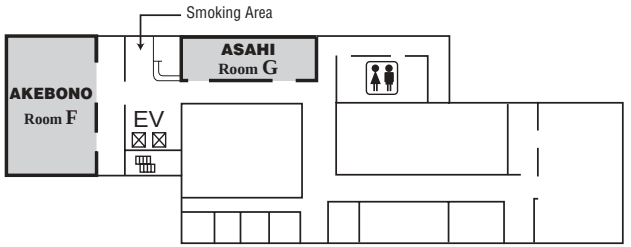
Conference Room C, D, E

43F



Conference Room F, G

47F



SSDM 2003 Condensed Program

Tuesday, September 16

EMINENCE HALL

9:30 - 12:00 PL: Opening Session

Room A	Room B	Room C	Room D	Room E	Room F	Room G
14:00-15:50 **A-1: Advanced Silicon Devices and Device Physics** -Gate Stack Technologies- (5 papers)	**14:00-16:00** **B-1: Non-Volatile Memory Technologies** -Non-Volatile Memory I- (5 papers)	**14:00-15:50** **C-1: Silicon Process / Materials Technologies** -High-k Gate Dielectric I- (5 papers)	**14:00-16:00** **D-1: New Materials and Characterization** -Oxide Reliability and Surface Characterization- (6 papers)	**14:00-16:00** **E-1: Quantum Nanostructure Devices and Physics** -Fabrication and Micromechanics- (7 papers)	**14:00-16:00** **F-1: Compound Semiconductor Materials and Devices** -III-V and Nitride Electron Devices- (7 papers)	**14:00-15:50** **G-1: Advanced Silicon Circuits and Systems** -Advanced CMOS Circuits and Systems- (5 papers)
16:15-18:15 **A-2: Advanced Silicon Devices and Device Physics** -Advanced CMOS Technology I- (6 papers)	**16:15-17:35** **B-2: Non-Volatile Memory Technologies** -Non-Volatile Memory II- (4 papers)	**16:15-17:55** **C-2: Silicon Process / Materials Technologies** -High-k Gate Dielectric II- (5 papers)	**16:15-18:15** **D-2: New Materials and Characterization** -Low k and Silicide Characterization- (6 papers)	**16:15-18:15** **E-2: Quantum Nanostructure Devices and Physics** -Nanostructured Optical Devices- (7 papers)	**16:15-18:00** **F-2: Compound Semiconductor Materials and Devices** -Nitride Electron Devices- (6 papers)	**16:15-17:45** **G-2: Advanced Silicon Circuits and Systems** -Collaboration of Circuits and Devices- (4 papers)

18:30-20:30 Banquet, Eminence Hall

Wednesday, September 17

Room A	Room B	Room C	Room D	Room E	Room F	Room G
9:00-10:30 **A-3: Advanced Silicon Devices and Device Physics** -High-k Technology I- (4 papers)	**9:00-10:20** **B-3: Non-Volatile Memory Technologies** -Non-Volatile Memory III- (3 papers)	**9:00-10:30** **C-3: Silicon Process / Materials Technologies** -Memory Technology- (4 papers)	**9:00-10:30** **D-3: Silicon-on-Insulator Technologies** -SOI Novel Devices- (4 papers)	**9:00-10:30** **E-3: Quantum Nanostructure Devices and Physics** -Characterization and Nanoprobing- (6 papers)	**9:00-10:30** **F-3: Compound Semiconductor Materials and Devices** -Novel Compound Semiconductors Devices- (4 papers)	**9:00-10:30** **G-3: Advanced Silicon Circuits and Systems** -Circuit Technologies for Emerging Technologies- (4 papers)
10:45-12:15 **A-4: Optoelectronic Devices and Photonic Crystal Devices** -VCSELs and Visible Lasers- (5 papers)	**10:45-12:05** **B-4: Non-Volatile Memory Technologies** -Non-Volatile Memory IV- (4 papers)	**10:45-12:05** **C-4: Silicon Process / Materials Technologies** -DRAM- (4 papers)	**10:45-12:05** **D-4: Silicon-on-Insulator Technologies** -SOI Device Physics- (4 papers)	**10:45-12:15** **E-4: Quantum Nanostructure Devices and Physics** -Spin-related Phenomena- (5 papers)	**10:45-12:15** **F-4: Compound Semiconductor Materials and Devices** -Optical Devices- (5 papers)	**10:45-12:00** **G-4: System-Level Integration and Packaging Technologies** -System-Level Integration and Packaging Technologies I- (4 papers)

13:00-15:00 Poster Session (OHGI)

15:15-16:45 **A-5: Optoelectronic Devices and Photonic Crystal Devices** -Optoelectronic Integrated Devices- (5 papers)	**15:15-16:45** **B-5: Organic Semiconductor Devices and Materials** -Preparation and Characterization- (6 papers)	**15:15-16:45** **C-5: Silicon Process / Materials Technologies** -Interconnect- (4 papers)	**15:15-16:45** **D-5: Silicon-on-Insulator Technologies** -Fin FET Technologies- (4 papers)	**15:15-16:30** **E-5: Quantum Nanostructure Devices and Physics** -Single Electron Transport- (4 papers)	**15:15-16:45** **F-5: Micro-Nano Electromechanical Devices for Bio- and Chemical Applications** -Micro-Nano Electro Mechanical Devices for Bio-and Chemical Applications I- (5 papers)	**15:15-16:45** **G-5: System-Level Integration and Packaging Technologies** -System-Level Integration and Packaging Technologies II- (4 papers)
17:00-18:15 **A-6: Optoelectronic Devices and Photonic Crystal Devices** -Lasers for Optical Communication- (4 papers)	**17:00-18:10** **B-6: Non-Volatile Memory Technologies** -Non-Volatile Memory V- (4 papers)	**17:00-18:20** **C-6: Silicon Process / Materials Technologies** -Interconnect- (4 papers)	**17:00-18:30** **D-6: New Materials and Characterization** -Si/SiGe Devices and Materials- (4 papers)	**17:00-18:30** **E-6: Novel Devices, Physics, and Fabrication** -Nanoprocess and Nanodevices- (5 papers)	**17:00-18:00** **F-6: Micro-Nano Electromechanical Devices for Bio- and Chemical Applications** -Micro-Nano Electro Mechanical Devices for Bio-and Chemical Applications II- (3 papers)	**17:00-18:15** **G-6: System-Level Integration and Packaging Technologies** -System-Level Integration and Packaging Technologies III- (4 papers)

18:45-20:45 Rump Session
Room A "Can channel material/structure engineering become a guiding principle for future CMOS device technology?"
Room B "What paradigm can nanoelectronic devices bring about?"

Thursday, September 18

Room A	Room B	Room C	Room D	Room E	Room F	Room G
9:00-10:30 **A-7: Advanced Silicon Devices and Device Physics** -High-k Technology II- (4 papers)	**9:00-10:20** **B-7: Silicon Process / Materials Technologies** -Metal Gate, Gate Oxde- (4 papers)	**9:15-10:30** **C-7: Organic Semiconductor Devices and Materials** -Organic Thin Film Transistor- (4 papers)	**9:05-10:30** **D-7: New Materials and Characterization** -Carbon Nanotube Devices and Materials- (4 papers)	**9:30-10:30** **E-7: Novel Devices, Physics and Fabrication** -Novel Materials and Devices- (4 papers)	**9:00-10:30** **F-7: Optoelectronic Devices and Photonic Crystal Devices** -Photonic Crystal Devices I- (5 papers)	**9:00-10:30** **G-7: SiGe/III-V/III-N Devices and Circuits for Wireless and Optical Communications** -III-V Devices & Circuits- (5 papers)
10:45-12:05 **A-8: Advanced Silicon Devices and Device Physics** -Advanced CMOS Technology II- (4 papers)	**10:45-12:05** **B-8: Silicon Process / Materials Technologies** -Si Process- (4 papers)	**10:45-12:00** **C-8: Organic Semiconductor Devices and Materials** -Organic Optics- (5 papers)	**10:45-12:10** **D-8: New Materials and Characterization** -High-k Dielectrics I- (5 papers)	**10:45-12:00** **E-8: Novel Devices, Physics and Fabrication** -Carbon Nanotubess- (4 papers)	**10:45-11:45** **F-8: Optoelectronic Devices and Photonic Crystal Devices** -Photonic Crystal Devices II- (3 papers)	**10:45-11:45** **G-8: SiGe/III-V/III-N Devices and Circuits for Wireless and Optical Communications** -SiGe Technologies- (3 papers)
13:30-14:50 **A-9: Advanced Silicon Devices and Device Physics** -Electron Mobility Characteristics- (4 papers)	**13:30-14:40** **B-9: Silicon-on-Insulator Technologies** -SOI Low Power Applications- (3 papers)	**13:30-14:45** **C-9: Organic Semiconductor Devices and Materials** -Molecular Devices and Materials- (4 papers)	**13:30-14:30** **D-9: New Materials and Characterization** -High-k Dielectrics II- (3 papers)	**13:30-14:45** **E-9: Novel Devices, Physics and Fabrication** -Si Nanowire and Dots- (5 papers)	**13:30-14:45** **F-9: Optoelectronic Devices and Photonic Crystal Devices** -Ultrafast Photonic Devices- (4 papers)	**13:30-14:45** **G-9: SiGe/III-V/III-N Devices and Circuits for Wireless and Optical Communications** -GaN Devices- (4 papers)
15:00-16:00 **A-10: Advanced Silicon Devices and Device Physics** -Poly-Si Device and Sensor- (3 papers)	**15:00-17:00** **B-10: Silicon-on-Insulator Technologies** -SOI CMOS Technologies- (6 papers)	**15:00-16:00** **C-10: Organic Semiconductor Devices and Materials** -Electroluminescent Devices and Materials- (4 papers)	**15:00-16:20** **D-10: New Materials and Characterization** -High-k DielectricsIII- (4 papers)	**15:00-16:15** **E-10: Novel Devices, Physics and Fabrication** -Quantum Computing Devices- (4 papers)	**15:00-16:00** **F-10: Optoelectronic Devices and Photonic Crystal Devices** -New Photonic Materials- (4 papers)	**15:00-16:00** **G-10: SiGe/III-V/III-N Devices and Circuits for Wireless and Optical Communications** -High Voltage Devices- (3 papers)

SSDM 2003 Chairpersons List

	Eminence Hall	Room A	Room B	Room C	Room D	Room E	Room F	Room G
Tuesday, September 16	**PL: (9:30-12:00)** S. Kawamura (AIST) M. Koyanagi (Tohoku Univ.)	**A-1: (14:00-15:50)** T. Mogami (NEC) K. Shibahara (Hiroshima Univ.)	**B-1: (14:00-16:00)** T. Nakamura (ROHM) Y. Shimada (Matsushita Electric)	**C-1: (14:00-15:50)** Y. Tsunashima (Toshiba) H. Kitajima (Selete)	**D-1: (14:00-16:00)** H. Satake (Toshiba) T. Maruizumi (Hitachi)	**E-1: (14:00-16:00)** Y. Hirayama (NTT) J. Motohisa (Hokkaido Univ.)	**F-1: (14:00-16:00)** T. Mizutani (Nagoya Univ.) M. Kuzuhara (FED)	**G-1: (14:00-15:50)** T. Kuroda (Keio Univ.) M. Fujishima (Univ. of Tokyo)
		A-2: (16:15-18:15) A. Hiroki (Kyoto Inst. of Technol.) S. Inaba (Toshiba)	**B-2: (16:15-17:35)** Y. Shimada (Matsushita Electric) T. Nakamura (ROHM)	**C-2: (16:15-17:55)** M. Kubota (Matsushita Electric) J. Yugami (Renesas)	**D-2: (16:15-18:15)** K. Kikuta (NEC) S. Zaima (Nagoya Univ.)	**E-2: (16:15-18:15)** K. Hirakawa (University of Tokyo) L. Samuelson (Lund Univ.)	**F-2: (16:15-18:00)** T. Kikkawa (Fujitsu Labs.) N. Maeda (NTT)	**G-2: (16:15-17:45)** M. Fujishima (Univ. of Tokyo) T. Kuroda (Keio Univ.)
Wednesday, September 17		**A-3: (9:00-10:30)** M. Ogawa (Kobe Univ.) T. Mogami (NEC)	**B-3: (9:00-10:20)** K. Takasaki (Fujitsu Labs.) H. Takada (Mitsubishi Electric)	**C-3: (9:00-10:30)** T. Kobayashi (Sony) I. Asano (Elpida)	**D-3: (9:00-10:30)** A. Ogura (NEC) T. Nakai (SUMCO)	**E-3: (9:00-10:30)** H. Akinaga (AIST) M. Sugawara (Univ. of Tokyo)	**F-3: (9:00-10:30)** K. Akimoto (Tsukuba Univ.) N. Kobayashi (Univ. of Electro-communications)	**G-3: (9:00-10:30)** K. Kotani (Tohoku Univ.) M. Takamiya (NEC)
		A-4: (10:45-12:15) S. Matsuo (NTT) G. Fish (Agility Communications)	**B-4: (10:45-12:05)** K. Yoshikawa (Toshiba) T. Kobayashi (Hitachi)	**C-4: (10:45-12:05)** M. Okuyama (Osaka Univ.) K. Hieda (Toshiba)	**D-4: (10:45-12:05)** O. Nishio (Sharp) T. J. King (UCB)	**E-4: (10:45-12:15)** A.T akeuchi (Waseda Univ.) T. Dietl (Polish Academy of Science)	**F-4: (10:45-12:15)** T. Matsuoka (NTT) M. Ikeda (Sony)	**G-4: (10:45-12:00)** K. Yasuda (Osaka Univ.) M. Kada (Sharp)
		A-5: (15:15-16:45) T. Nishimura (Mitsubishi Electric) S. Lee (KIST)	**B-5: (15:15-16:45)** F. Kaneko (Niigata Univ.) S. Yamada (Kyushu Univ.)	**C-5: (15:15-16:45)** N. Kobayashi (SLETE) T. Nakamura (Fujitsu)	**D-5: (15:15-16:45)** H. Matsuhashi (Oki Electric) K. Rim (IBM)	**E-5: (15:15-16:30)** Y. Ohno (Tohoku Univ.) A. Shields (Toshiba Research Europe)	**F-5: (15:15-16:45)** Y. Miyahara (NIMS) M. Kamahori (Hitachi)	**G-5: (15:15-16:45)** K. Takahashi (ASET) M. Kimura (Renesas)
		A-6: (17:00-18:15) H. Shimizu (Furukawa Electric.) M. Nielsen (Denmark Tech. Univ.)	**B-6: (17:00-17:40)** N. Ajika (GENUSION) H. Takada (Mitsubishi Electric)	**C-6: (17:00-18:20)** K. Kikuta (NEC) J. Koike (Tohoku Univ.)	**D-6: (17:00-18:30)** J. Murota (Tohoku Univ.) A. Sakai (Nagoya Univ.)	**E-6: (17:00-18:30)** M. Tabe (Shizuoka Univ.) Y. Takahashi (NTT)	**F-6: (17:00-18:00)** H. Tabata (Osaka Univ.) K. Shimoide (Asahi KASEI)	**G-6: (17:00-18:15)** M. Aoyagi (AIST) H. Ezawa (Toshiba)
Thursday, September 18		**A-7: (9:00-10:30)** K. Shibahara (Hiroshima Univ.) M. Ogawa (Kobe Univ.)	**B-7: (9:00-10:20)** T. Arikado (SELETE) K. Suguro (Toshiba)	**C-7: (9:15-10:30)** T. Kamata (AIST) S. Shiratori (Keio Univ.)	**D-7: (9:05-10:30)** Y. Awano (Fujitsu Labs.) Y. Ochiai (NEC)	**E-7: (9:30-10:30)** Y. Kuwahara (Osaka Univ.) H. Yamaguchi (NTT)	**F-7: (9:00-10:30)** N. Yokouchi (Furukawa Electric) T. Baba (Yokohama National Univ.)	**G-7: (9:00-10:30)** Y. Tateno (Fujitsu Quantum Devices Ltd.) Y. J. Chan (National Central Univ.)
		A-8: (10:45-12:05) T. Eimori (Renesas) K. Goto (Fujitsu Labs.)	**B-8: (10:45-12:05)** M. Hori (Nagoya Univ.) T. Horikawa (MIRAI-ASRC)	**C-8: (10:45-12:00)** K. Kudo (Chiba Univ.) C. Adachi (CIST)	**D-8: (10:45-12:10)** S. Miyazaki (Hiroshima Univ.) K. Torii (SELETE)	**E-8: (10:45-12:00)** Y. Homma (NTT) F. Nihey (NEC)	**F-8: (10:45-11:45)** H. Yamada (NEC) T. Katsuyama (Univ. of Tokyo)	**G-8: (10:45-11:45)** K. Washio (Hitachi) N. Suematsu (Mitsubishi Electric)
		A-9: (13:30-14:50) S. Inaba (Toshiba) N. Sugii (Hitachi)	**B-9: (13:30-14:40)** K. Ino (Toshiba) T. Ipposhi (Renesas)	**C-9: (13:30-14:45)** M. Iwamoto (Tokyo Inst. of Technol.) A. Sugimura (Osaka Sangyo Univ.)	**D-9: (13:30-14:30)** T. Nabatame (MIRAI-ASET) Y. Sugita (Fujitsu)	**E-9: (13:30-14:45)** Y. Miyamoto (Tokyo Inst. of Technol.) S. Miyazaki (Hiroshima Univ.)	**F-9: (13:30-14:45)** N. Suzuki (Toshiba) S. Arahira (Oki Electric)	**G-9: (13:30-14:45)** M. Kuzuhara (FED) Y. Ohno (Tokusima Univ.)
		A-10: (15:00-16:00) N. Sugii (Hitachi) T. Eimori (Renesas)	**B-10: (15:00-17:00)** Y. Kado (NTT) M. Terauchi (Hiroshima City Univ.)	**C-10: (15:00-16:00)** Y. Ohmori (Osaka Univ.) K. Kudo (Chiba Univ.)	**D-10: (15:00-16:20)** M. Hiratani (Hitachi) H. Watanabe (NEC)	**E-10: (15:00-16:15)** K. Ishibashi (RIKEN) Y. Pashkin (NEC)	**F-10: (15:00-16:00)** O. Wada (Kobe Univ.) T. Mizumoto (Tokyo Inst. of Technol.)	**G-10: (15:00-16:00)** K. Morizuka (Toshiba) T. Enoki (NTT)